



ZHEJIANG UNIU-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



U2104B Data Sheet

V 1.1

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High Current IO+/- 2.0/2.5A HALF-BRIDGE DRIVER

General Description

The U2104B Fully operated to +600V is high voltage, high speed power MOSFET and IGBT driver with dependent high and low side referenced output channels.

The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Product Summary

V _{OFFSET}	600V max
I _{O+/-}	2.0A / 2.5A
V _{OUT}	5V ~ 20V
t _{on/off} (typ.)	320/200ns
Deadtime (typ.)	120ns
Work Tem	-40 ~125°C

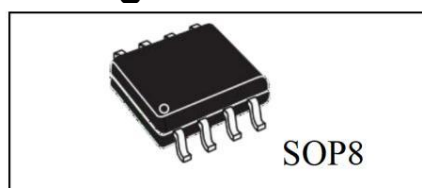
Key Features

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 5 to 20V
- Undervoltage lockout
- 3.3V, 5V input logic compatible
- Cross-conduction prevention logic
- internally set deadtime
- High side output in phase with input
- Shut down input turns off both channels
- Matched propagation delay for both channels

Applications

- Home appliances
- Industrial applications and drives
- Motor drivers
- DC, AC, PMDC and PMAC motors
- Induction heating
- HVAC

Packages

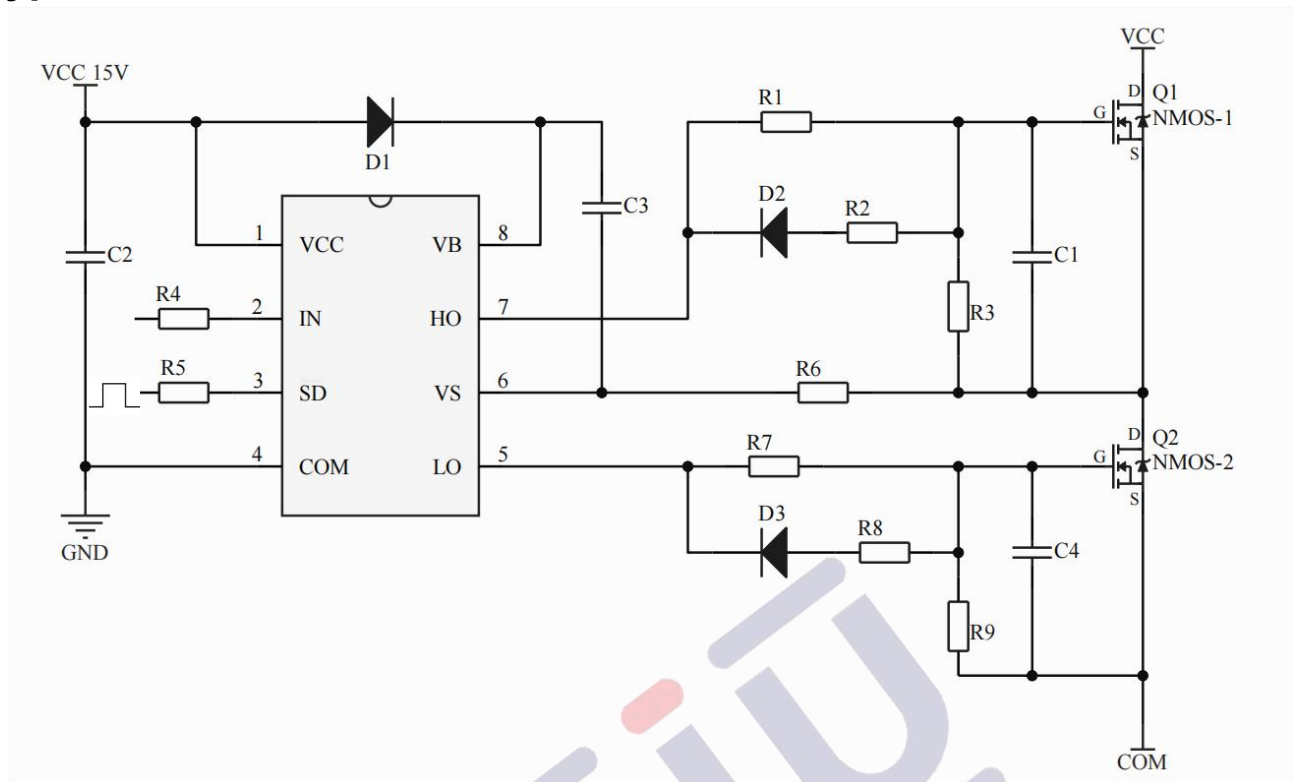


SOP8

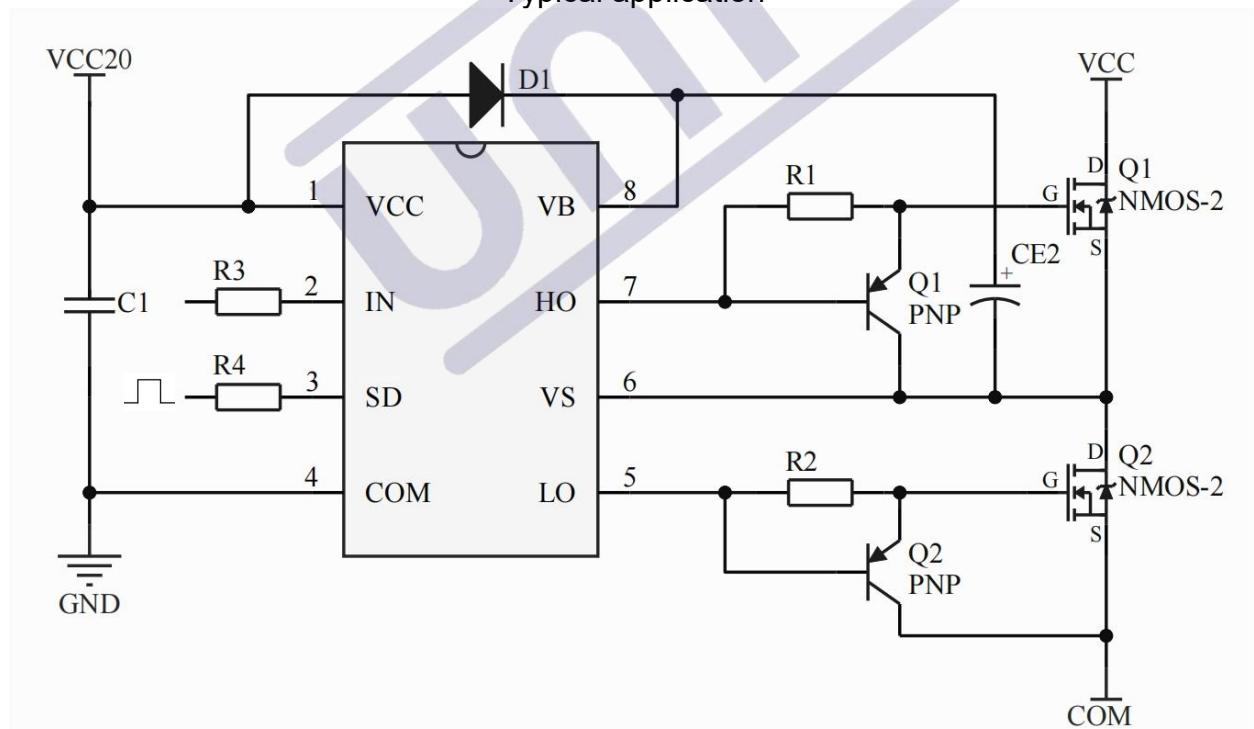
Product information

Base Part Number	Package Type	Standard OUT		V _{OFFSET}	Logic Control
		IO+	IO-		
U2104B	SOP8	2.0A	2.5A	600V	IN & SD

Typical Connection



Typical application



Much Big POWER application

Note: The above circuits and parameters are for reference only. The actual application circuit should be designed with the measured results in setting the paramete

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
VB	High side floating absolute voltage	-0.3	600	V
VS	High side floating supply offset voltage	VB-20	VB+0.3	
VHO	High side floating output voltage	VS-0.3	VB+0.3	
VLO	Low side output voltage	-0.3	VCC + 0.3	
VCC	Low side and logic fixed supply voltage	-0.3	20	
VIN	Logic input voltage (IN & SD)	-0.3	Vcc+0.3	
dVS/dt	Allowable offset supply voltage transient	—	55	V/ns
P _D	Package power dissipation @ TA ≤ +25°C	—	0.625	W
RthJA	Thermal resistance, junction to ambient	—	200	°C/W
TJ	Junction temperature	—	150	°C
TS	Storage temperature	-55	175	
TL	Lead temperature (soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure. For proper operation the device should be used within the recommended conditions. The VS offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	VS + 5	VS + 20	V
VS	High side floating supply offset voltage	-6(Note1)	600	
VHO	High side floating output voltage	VS	VB	
VLO	Low side output voltage	0	VCC	
VCC	Low side and logic fixed supply voltage	5.0	20	
VIN	Logic input voltage (IN&SD)	0	VCC	
TA	Ambient temperature	-40	125	°C

Note1: Logic operational for VS of -6 to +600V. Logic state held for VS of -6V to -VBS.

Electrical Characteristic

$V_{CC} = V_{BS} = V_{BIAS} = 15V$, $C_L = 1000pF$, $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
tr	Turn-on rise time	—	20	—	ns	
tf	Turn-off fall time	—	18	—		
ton	Turn-on propagation delay	—	320	—		VS = 0V
toff	Turn-off propagation delay	—	200	—		VS = 400V
tsd	Shutdown propagation delay	—	200	—		
DT	Deadtime, LS turn-off to HS turn-on & HS turn-on to LS turn-off	—	120	—		
MT	Delay matching, HS & LS turn-on/off	—	—	70		

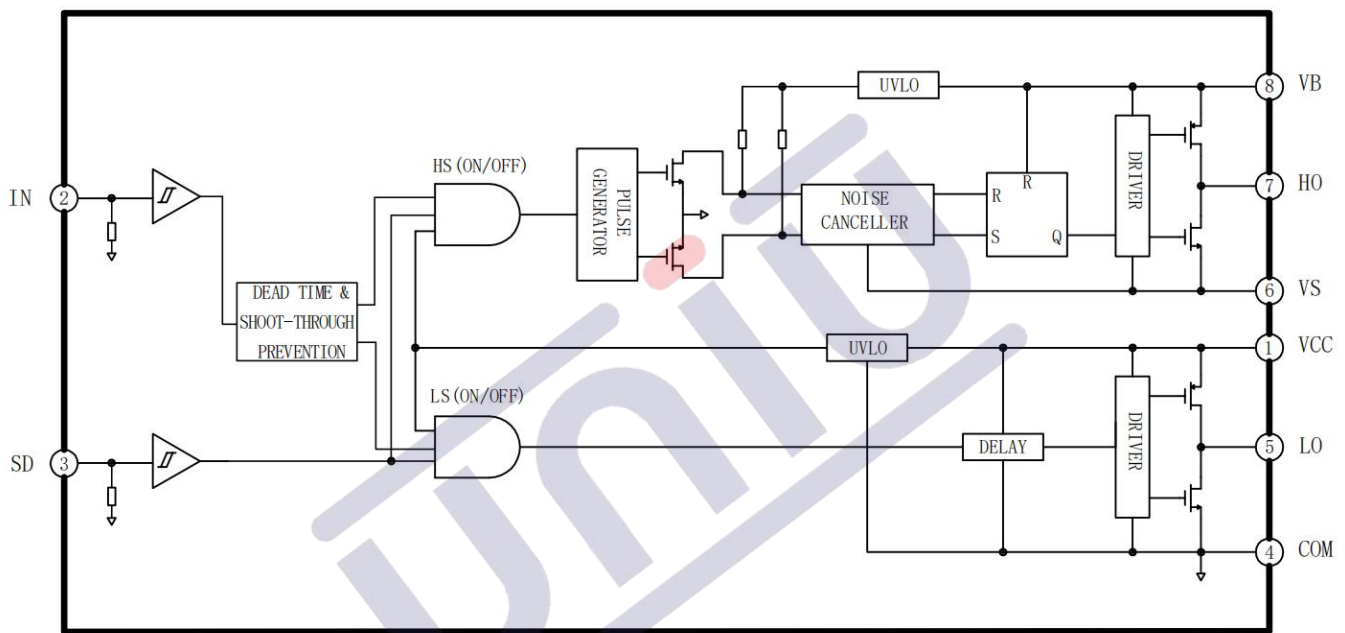
Electrical Characteristic

$V_{CC} = V_{BS} = V_{BIAS} = 15V$, $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions	
Low Side Power Supply Characteristics							
V _{CCUV+}	VCC supply undervoltage positive going threshold	—	4.9	—	V		
V _{CCUV-}	VCC supply undervoltage negative going threshold	—	4.6	—			
V _{CCHYS}	VCC supply under-voltage lockout hysteresis	—	0.3	—			
High Side Floating Power Supply Characteristics							
V _{BSUV+}	VBS supply undervoltage positive going threshold	—	4.8	—	V		
V _{BSUV-}	VBS supply undervoltage negative going threshold	—	4.7	—			
V _{BSUVHS}	High side VBS supply under-voltage lockout hysteresis	—	0.1	—			
IQCC	Quiescent VCC supply current	—	120	—	uA		
IQBS	Quiescent VBS supply current	—	35	—			
ILK	Offset supply leakage current	—	—	3		VB =VS =400V	
VIH	Logic “1” (HO) input voltage	3	—	—	V	VCC =5V to 20V	
VIL	Logic “0” (HO) input voltage	—	—	0.8		VCC =5V to 20V	
VSD	SD input positive going threshold	3	—	—		VCC =5V to 20V	
VSD	SD input negative going threshold	—	—	0.8		VCC =5V to 20V	
IIN+	Logic “1” input bias current	—	20	50	uA	V _{IN} =5V	
IIN-	Logic “0” input bias current	—	—	1		V _{IN} =0V	

VOH	High level output voltage, $V_{BIAS} - V_O$	—	—	100	mV	$I_o = 0A$
VOL	Low level output voltage, V_O	—	—	100		$I_o = 0A$
IO+	Output high short circuit pulsed current	—	2.0	—	A	$V_O = 0V, V_{IN} = V_{IH}$ $PW \leq 10\ \mu s$
IO-	Output low short circuit pulsed current	—	2.5	—		$V_O = 15V, V_{IN} = V_{IL}$ $PW \leq 10\ \mu s$

Block Diagram



Truth Table

IN	SD	HO	LO	logic diagram
0	0	0	0	
1	1	1	0	
0	1	0	1	
1	0	0	0	

Time waveform

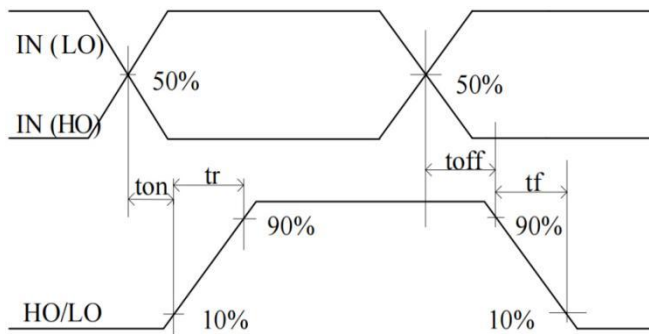


Figure 1. Switching Time Waveform Definitions

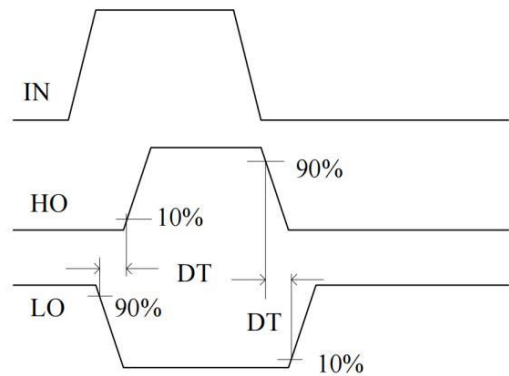


Figure 2. Deadtime Waveform Definitions

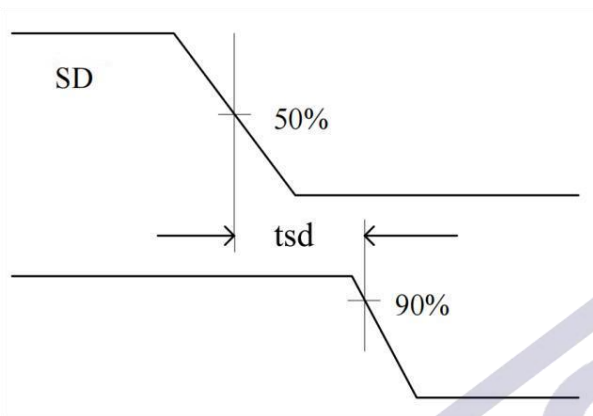


Figure 3. Shutdown Waveform Definitions

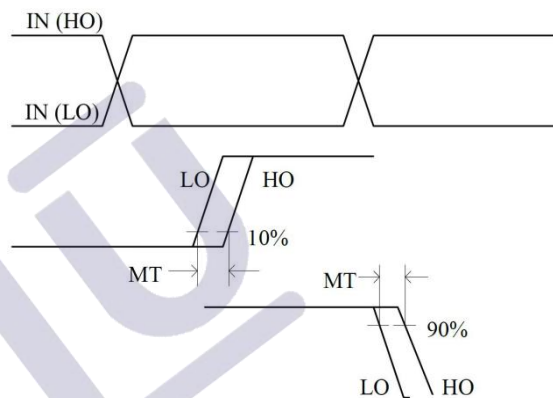


Figure 4. Delay matching time Definitions

1、版本记录

DATE	REV.	DESCRIPTION
2021/04/19	1.0	首次发布
2022/05/21	1.1	布局调整

2、免责声明

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